

isc Silicon NPN Power Transistor

2SD1352

DESCRIPTION

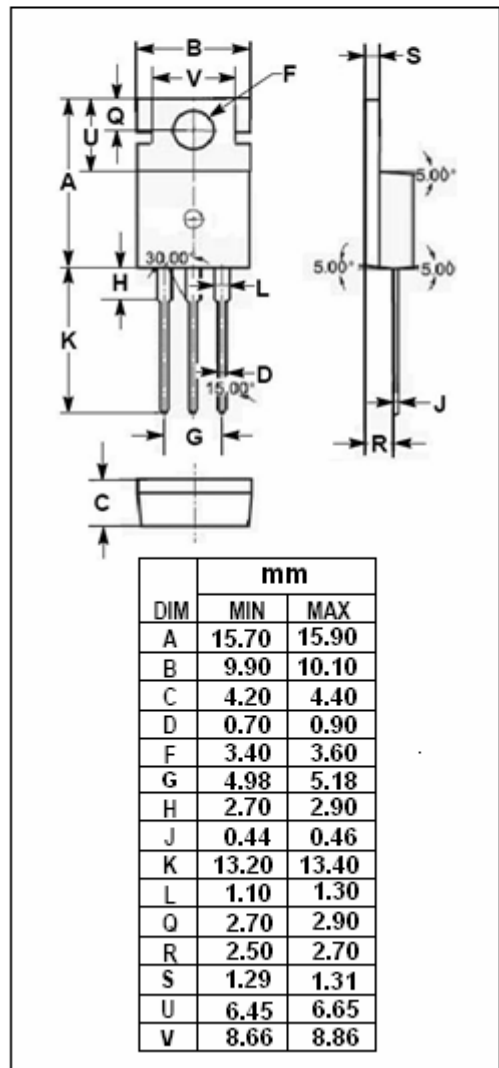
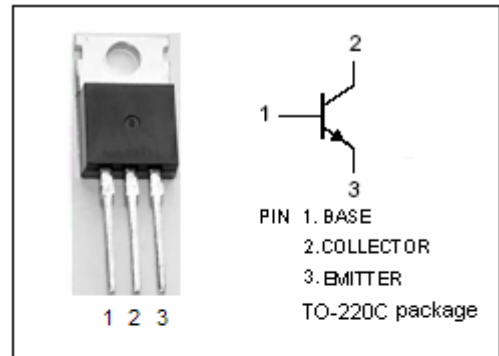
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 80(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SB989

APPLICATIONS

- Designed for general purpose application

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_E	Emitter Current-Continuous	-4	A
I_B	Base Current-Continuous	0.4	A
P_C	Collector Power Dissipation@ $T_C=25^\circ\text{C}$	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SD1352****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}; I_B=0$	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\text{mA}; I_C=0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$		0.45	1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=3\text{A}; V_{CE}=5\text{V}$		1.0	1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			30	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			0.1	mA
h_{FE-1}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	40		240	
h_{FE-2}	DC Current Gain	$I_C=3\text{A}; V_{CE}=5\text{V}$	15	50		
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$		90		pF
f_T	Current-Gain—Bandwidth Product	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	3	8		MHz

◆ **h_{FE-1} Classifications**

R	O	Y
40-80	70-140	120-240